

# FDMS7680

## N-Channel PowerTrench® MOSFET

30 V, 6.9 mΩ

### Features

- Max  $r_{DS(on)} = 6.9 \text{ m}\Omega$  at  $V_{GS} = 10 \text{ V}$ ,  $I_D = 14 \text{ A}$
- Max  $r_{DS(on)} = 11 \text{ m}\Omega$  at  $V_{GS} = 4.5 \text{ V}$ ,  $I_D = 11 \text{ A}$
- Advanced Package and Silicon combination for low  $r_{DS(on)}$  and high efficiency
- Next generation enhanced body diode technology, engineered for soft recovery.
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

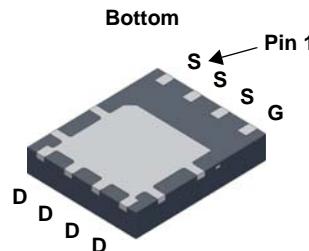


### General Description

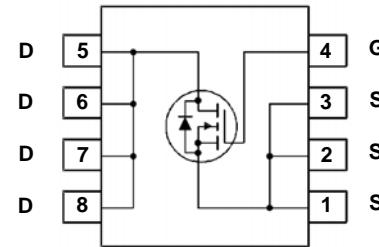
This N-Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $r_{DS(on)}$ , fast switching speed and body diode reverse recovery performance.

### Applications

- IMVP Vcore Switching for Notebook
- VRM Vcore Switching for Desktop and Server
- O-ringFET / Load Switch
- DC-DC Conversion



Power 56



### MOSFET Maximum Ratings $T_A = 25 \text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	30	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous (Package limited) $T_C = 25 \text{ }^\circ\text{C}$	28	A
	-Continuous (Silicon limited) $T_C = 25 \text{ }^\circ\text{C}$	53	
	-Continuous $T_A = 25 \text{ }^\circ\text{C}$ (Note 1a)	14	
	-Pulsed	80	
$E_{AS}$	Single Pulse Avalanche Energy (Note 3)	29	mJ
$P_D$	Power Dissipation $T_C = 25 \text{ }^\circ\text{C}$	33	W
	Power Dissipation $T_A = 25 \text{ }^\circ\text{C}$ (Note 1a)	2.5	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.7	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS7680	FDMS7680	Power 56	13 "	12 mm	3000 units

## Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$\text{BV}_{\text{DSS}}$	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}$	30			V
$\frac{\Delta \text{BV}_{\text{DSS}}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , referenced to $25^\circ\text{C}$		13		$\text{mV}/^\circ\text{C}$
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	$\mu\text{A}$
$I_{\text{GSS}}$	Gate to Source Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	$\text{nA}$

### On Characteristics

$V_{GS(\text{th})}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	1.25	1.9	3.0	V
$\frac{\Delta V_{GS(\text{th})}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , referenced to $25^\circ\text{C}$		-6		$\text{mV}/^\circ\text{C}$
$r_{DS(\text{on})}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 14 \text{ A}$		5.6	6.9	$\text{m}\Omega$
		$V_{GS} = 4.5 \text{ V}, I_D = 11 \text{ A}$		8.0	11	
		$V_{GS} = 10 \text{ V}, I_D = 14 \text{ A}, T_J = 125^\circ\text{C}$		7.3	10.1	
$g_{\text{FS}}$	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_D = 14 \text{ A}$		85		s

### Dynamic Characteristics

$C_{\text{iss}}$	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1390	1850	pF
$C_{\text{oss}}$	Output Capacitance			430	575	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance			60	85	pF
$R_g$	Gate Resistance			0.9	2.0	$\Omega$

### Switching Characteristics

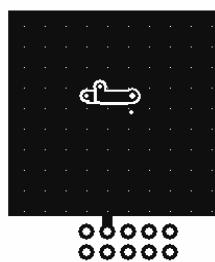
$t_{d(\text{on})}$	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, I_D = 14 \text{ A}, V_{GS} = 10 \text{ V}, R_{\text{GEN}} = 6 \Omega$		10	20	ns
$t_r$	Rise Time			4	10	ns
$t_{d(\text{off})}$	Turn-Off Delay Time			21	34	ns
$t_f$	Fall Time			3	10	ns
$Q_g$	Total Gate Charge	$V_{GS} = 0 \text{ V} \text{ to } 10 \text{ V}$		20	28	nC
	Total Gate Charge	$V_{GS} = 0 \text{ V} \text{ to } 4.5 \text{ V}$	$V_{DD} = 15 \text{ V}, I_D = 14 \text{ A}$	9	13	
$Q_{gs}$	Gate to Source Charge	4.6			nC	
$Q_{gd}$	Gate to Drain "Miller" Charge	2.3			nC	

### Drain-Source Diode Characteristics

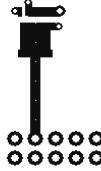
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 2.1 \text{ A}$ (Note 2)		0.74	1.2	V
		$V_{GS} = 0 \text{ V}, I_S = 14 \text{ A}$ (Note 2)		0.83	1.3	
$t_{rr}$	Reverse Recovery Time	$I_F = 14 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$		24	39	ns
				8	15	nC
$Q_{rr}$	Reverse Recovery Charge	$I_F = 14 \text{ A}, di/dt = 300 \text{ A}/\mu\text{s}$		20	36	ns
				15	27	nC

#### Notes:

1.  $R_{\text{thJA}}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\text{thJC}}$  is guaranteed by design while  $R_{\text{thCA}}$  is determined by the user's board design.



a. 50 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



b. 125 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty cycle < 2.0%.

3. Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.3 \text{ mH}$ ,  $I_{AS} = 14 \text{ A}$ ,  $V_{DD} = 27 \text{ V}$ ,  $V_{GS} = 10 \text{ V}$ .

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

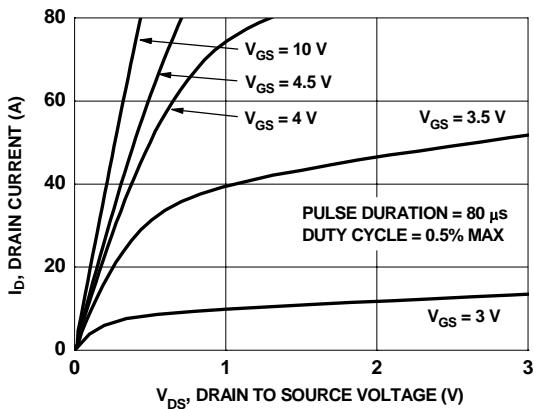


Figure 1. On Region Characteristics

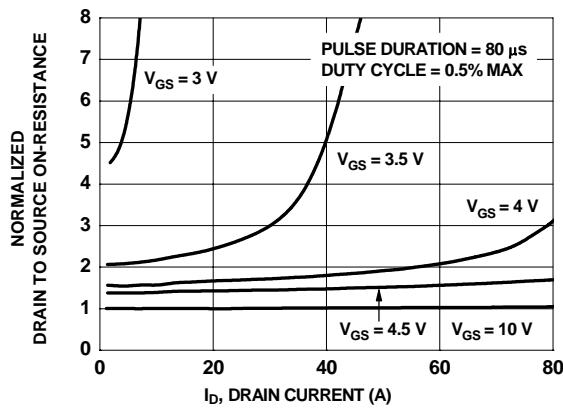


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

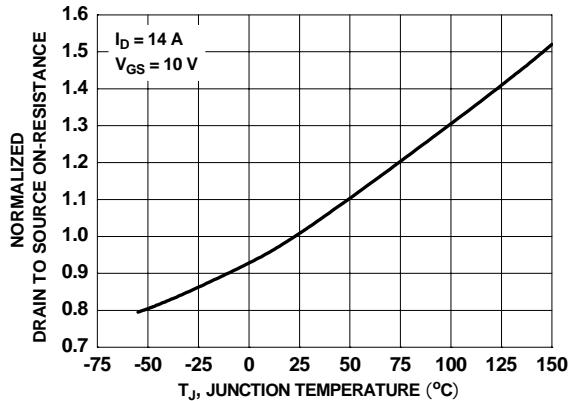


Figure 3. Normalized On Resistance vs Junction Temperature

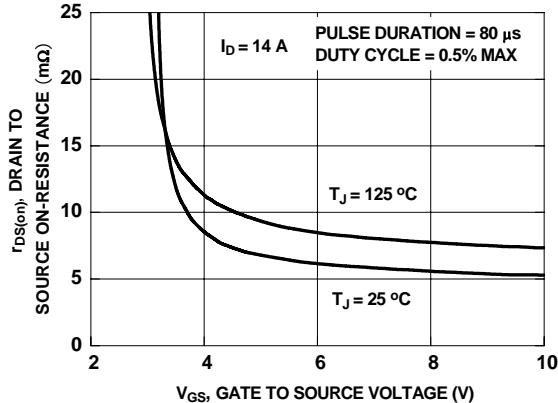


Figure 4. On-Resistance vs Gate to Source Voltage

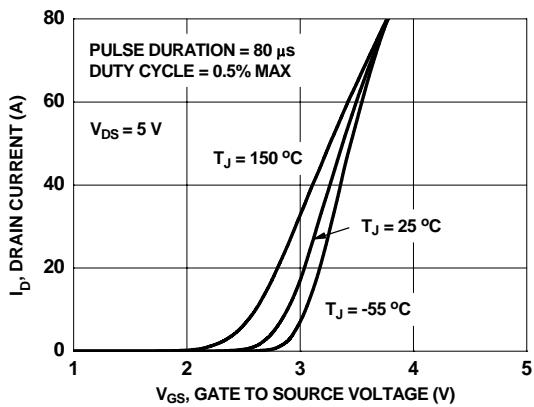


Figure 5. Transfer Characteristics

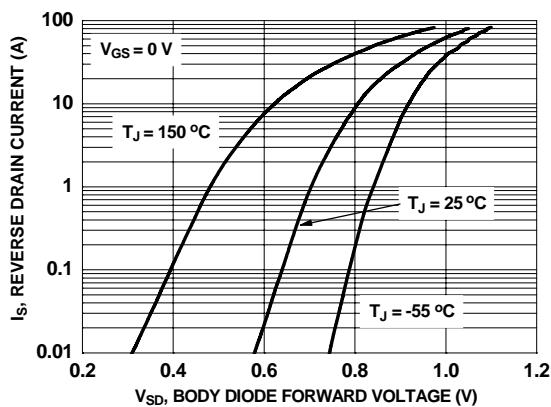


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

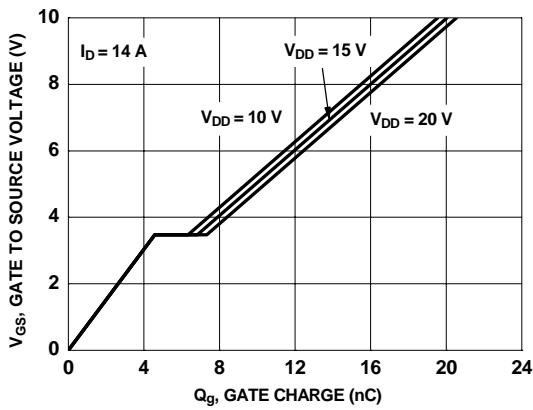


Figure 7. Gate Charge Characteristics

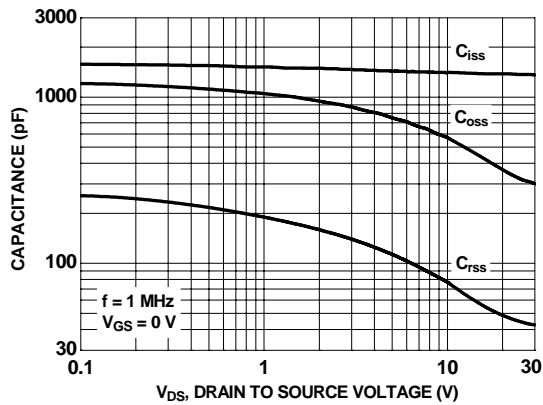


Figure 8. Capacitance vs Drain to Source Voltage

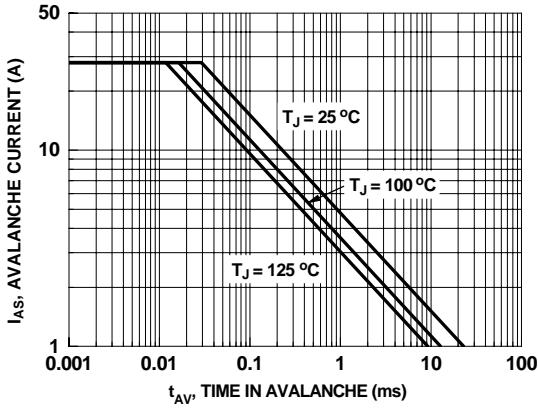


Figure 9. Unclamped Inductive Switching Capability

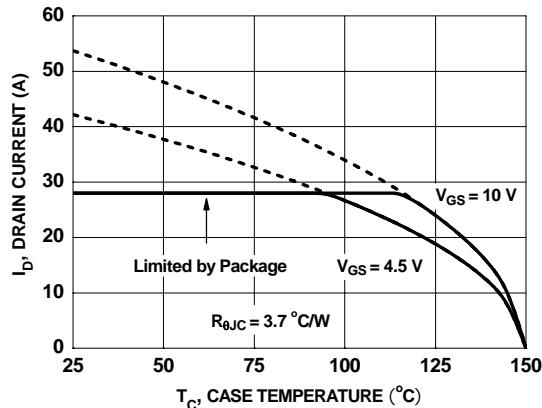


Figure 10. Maximum Continuous Drain Current vs Case Temperature

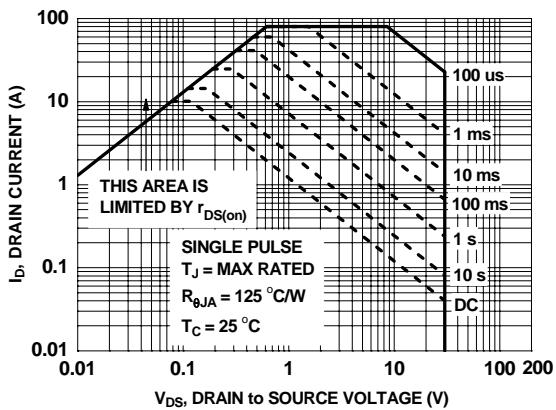


Figure 11. Forward Bias Safe Operating Area

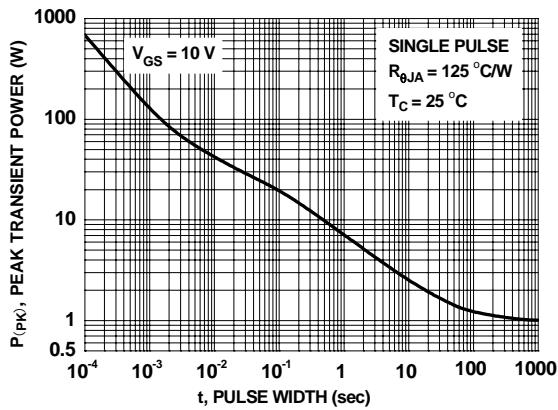


Figure 12. Single Pulse Maximum Power Dissipation

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

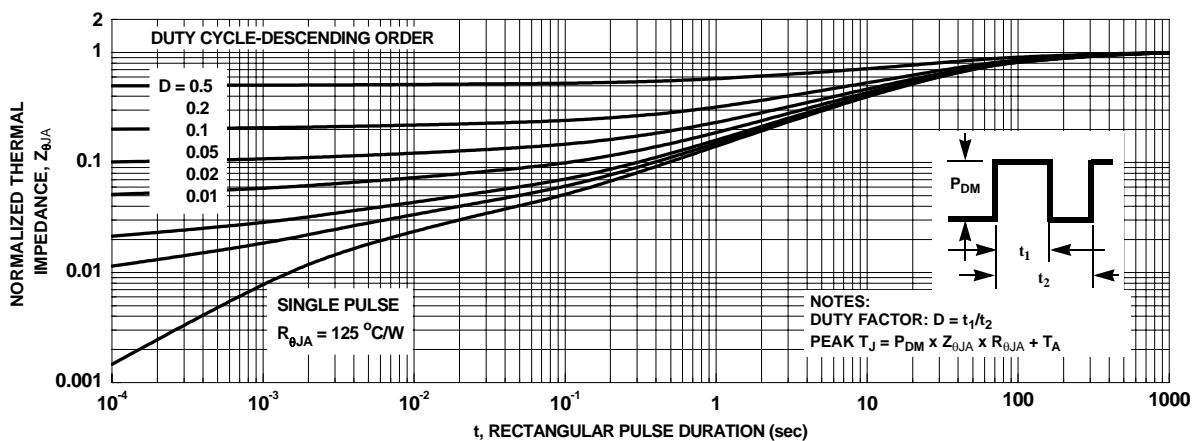


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

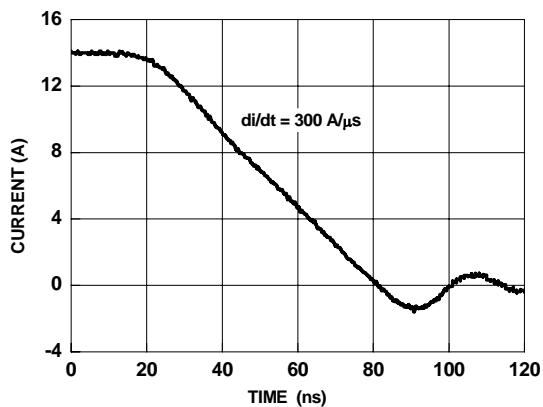
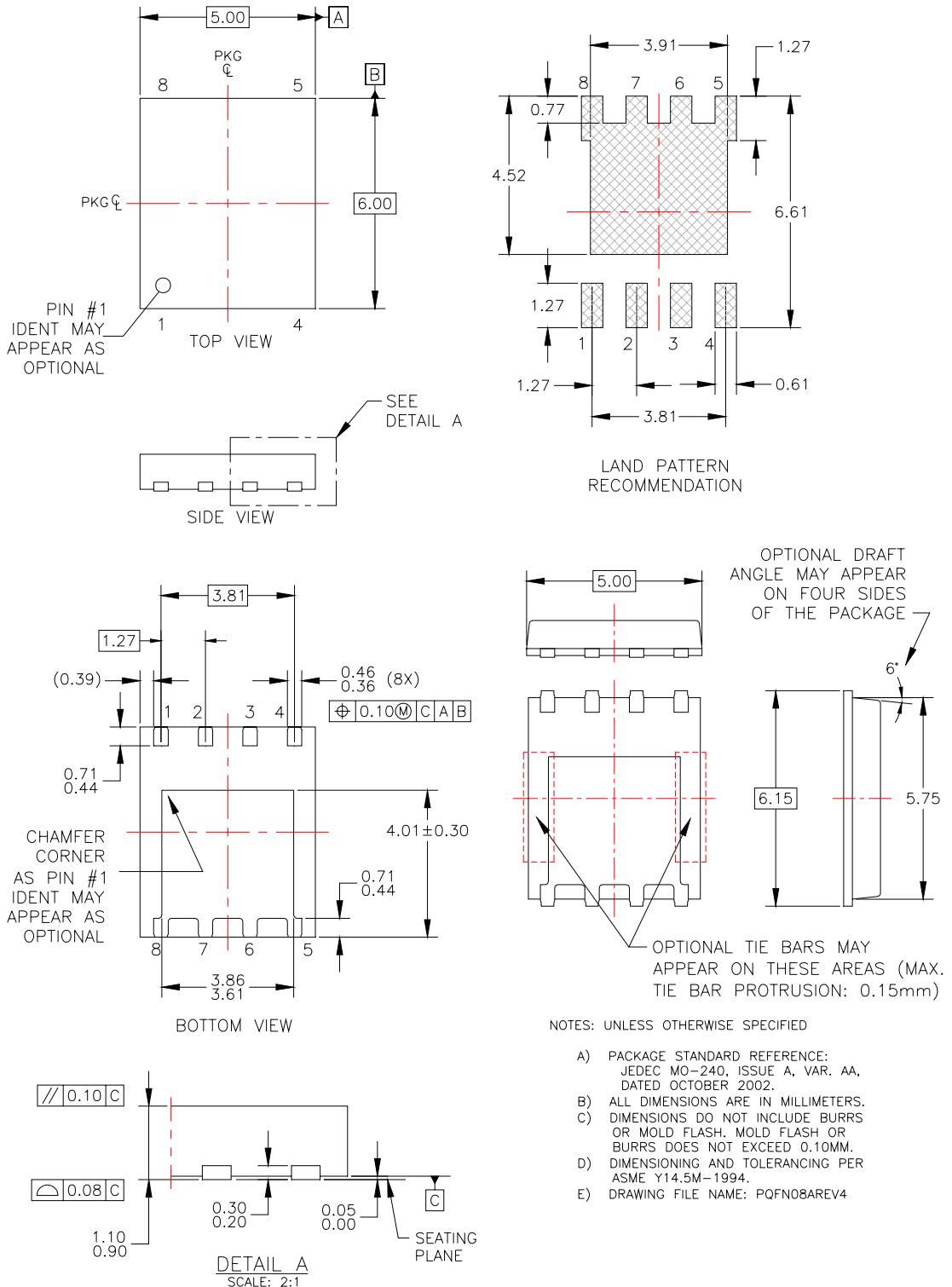


Figure 14. Body Diode Reverse Recovery Characteristics

Dimensional Outline and Pad Layout





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